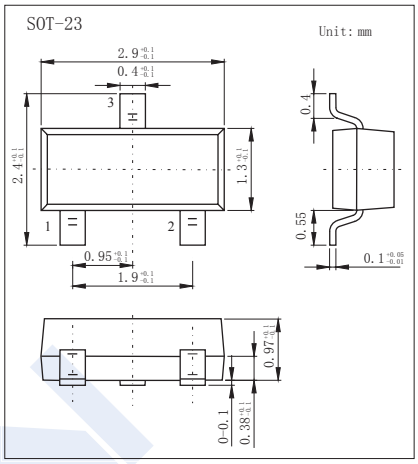
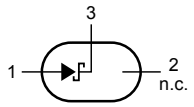
Schottky Diodes

BAS70-04/05/06 (KAS70-04/05/06)

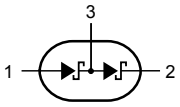


■ Features

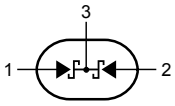
- Fast Switching Speed
- High breakdown voltage



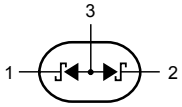
BAS70 single diode.



BAS70-04



BAS70-05



BAS70-06

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_{RM}	70	V
Peak Reverse Voltage	V_{RRM}	70	
Average Rectified Current at Temp=25℃	I_{FAV}	70	mA
Non-Repetitive Peak Forward Surge Current t=1s	I_{FSM}	100	
Power Dissipation	P_d	215	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	I_R= 10 uA	70			V
Forward voltage	V_{F1}	I_F= 1 mA			0.41	
	V_{F2}	I_F= 10 mA			0.75	
	V_{F3}	I_F= 15 mA			1	
Reverse voltage leakage current	I_{R1}	V_R= 70 V			1	uA
	I_{R2}	V_R= 50 V			0.1	
Junction capacitance	C_j	V_R= 0 V, f= 1 MHz			2	pF

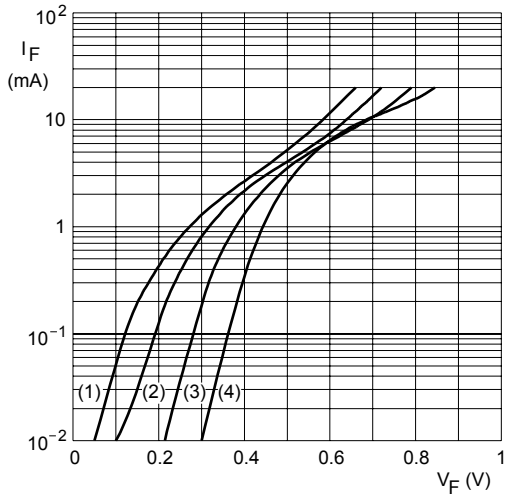
■ Marking

NO.	BAS70	BAS70-04	BAS70-05	BAS70-06
Marking	73P*	74P*	75P*	76P*

Schottky Diodes

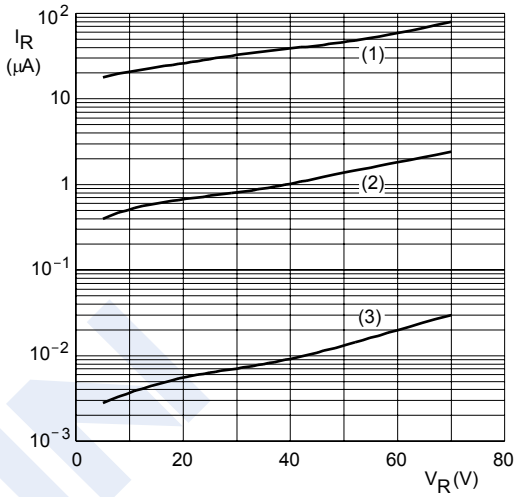
BAS70-04/05/06 (KAS70-04/05/06)

■ Typical Characterisitics



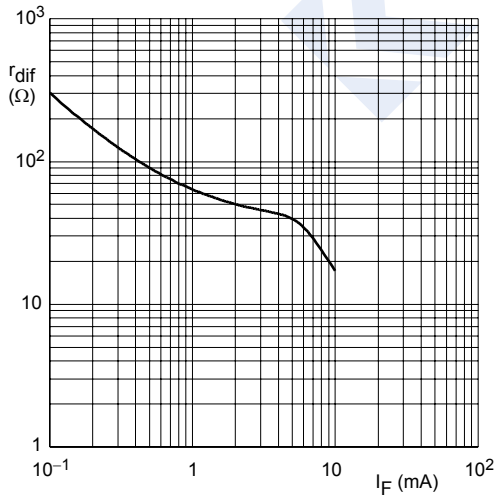
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig.1 Forward current as a function of forward voltage; typical values.



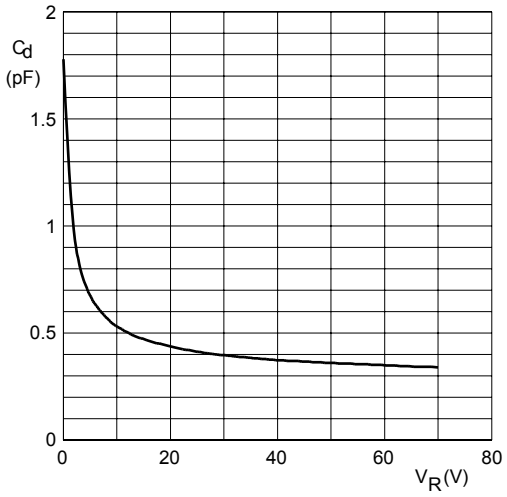
(1) T_{amb} = 150 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.

Fig.2 Reverse current as a function of reverse voltage; typical values.



f = 10 kHz.

Fig.3 Differential forward resistance as a function of forward current; typical values.



f = 1 MHz.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.